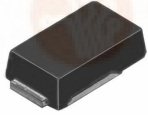




# S1PA thru S1PJ

Vishay Semiconductors  
formerly General Semiconductor

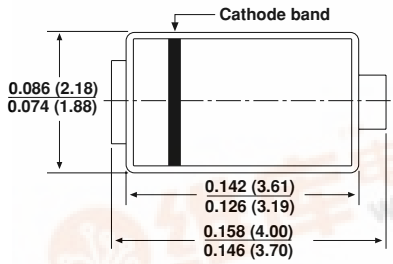
New Product



Case Style SMP

## High Current Density Surface Mount Glass-Passivated Rectifiers

Reverse Voltage 50 to 600 V  
Forward Current 1.0 A



### Features

- Very low profile - typical height of 1.0mm
- Ideal for automated placement
- Glass passivated chip junction
- For use in rectification, power supply, home appliances and telecommunication
- High temperature soldering:  
260°C maximum/10 seconds at terminals
- Meets MSL level 1 per J-STD-020C

### Mechanical Data

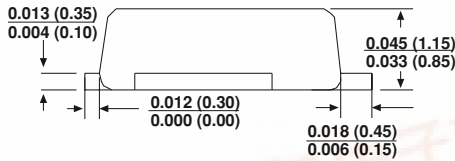
Case: SMP

Terminals: Matte Tin plated (E3 Suffix) leads, solderable per J-STD-002B and MIL-STD-750, Method 2026

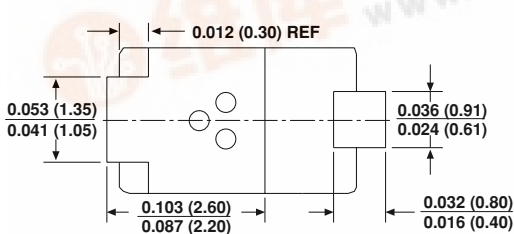
Polarity: Color band denotes cathode end

Weight: 0.0009 oz., 0.024 g

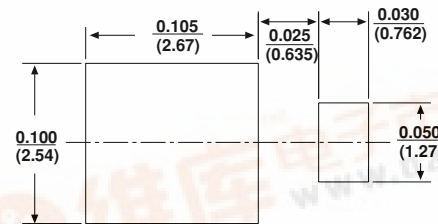
Epoxy meets UL 94V-0 flammability rating



### Mounting Pad Layout



Dimensions in inches and (millimeters)



### Maximum Ratings & Thermal Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	S1PA	S1PB	S1PD	S1PG	S1PJ	Unit
Device marking code		SA	SB	SD	SG	SJ	
Maximum reverse voltage	V <sub>RM</sub>	50	100	200	400	600	V
Maximum average forward rectified current Fig.1	I <sub>F(AV)</sub>	1					A
Peak forward surge current 10ms single half sine-wave superimposed on rated load	I <sub>FSM</sub>	30					A
Typical thermal resistance <sup>(1)</sup>	R <sub>θJA</sub> R <sub>θJL</sub> R <sub>θJC</sub>	105 15 20					°C/W
Operating junction temperature	T <sub>J</sub>	150					°C
Storage temperature	T <sub>STG</sub>	-55 to +150					°C

### Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Maximum instantaneous forward voltage <sup>(2)</sup> at I <sub>F</sub> =1A, T <sub>J</sub> =25°C at I <sub>F</sub> =1A, T <sub>J</sub> =125°C	V <sub>F</sub>	1.1 0.95	V
Maximum reverse current at rated V <sub>R</sub> <sup>(2)</sup> T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>R</sub>	1.0 50	µA
Typical reverse recovery time at at I <sub>F</sub> = 0.5A, I <sub>R</sub> = 1.0A, I <sub>rr</sub> = 0.25A	t <sub>rr</sub>	1.8	µs
Typical junction capacitance at 4.0V, 1MHz	C <sub>J</sub>	6.0	pF

Notes: (1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0mm copper pad areas. R<sub>θJL</sub> is measured at the terminal of cathode band. R<sub>θJC</sub> is measured at the top centre of the body  
(2) Pulse test: 300µs pulse width, 1% duty cycle

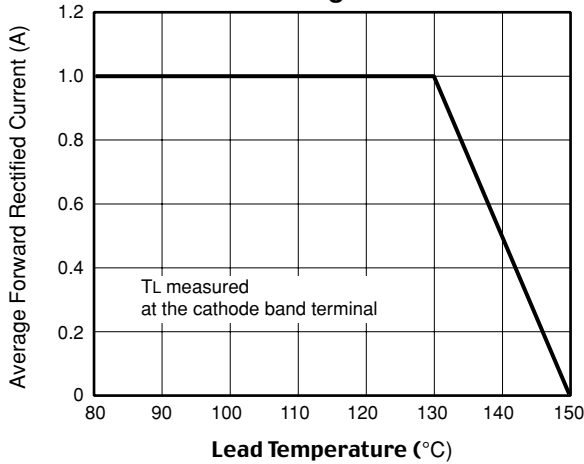
# S1PA thru S1PJ



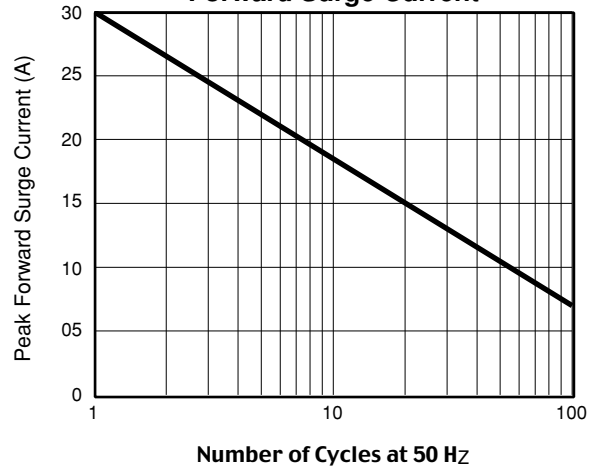
Vishay Semiconductors  
formerly General Semiconductor

## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

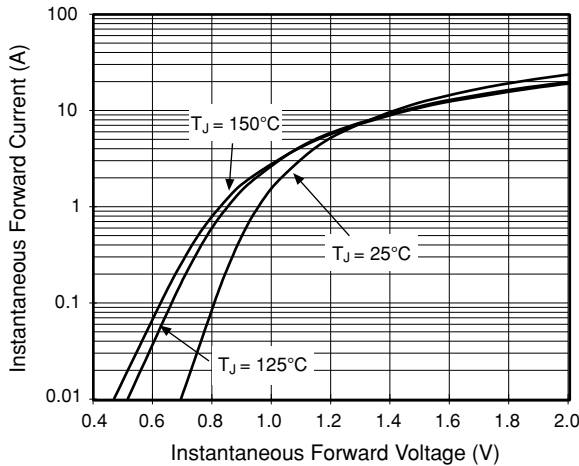
**Fig. 1 – Maximum Forward Current Derating Curve**



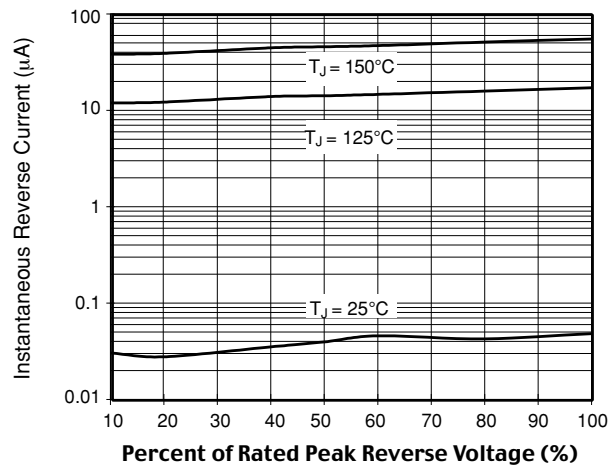
**Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current**



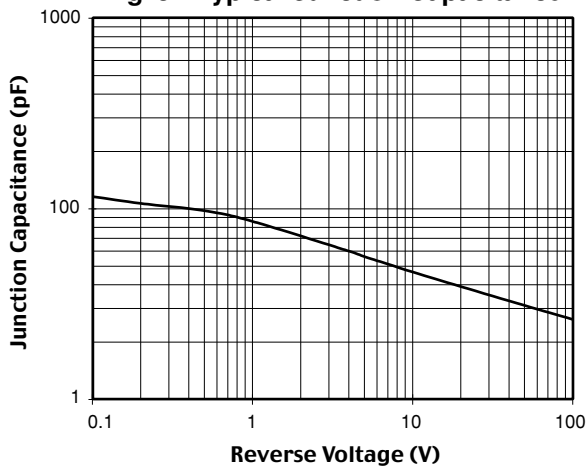
**Fig. 3 – Typical Instantaneous Forward Characteristics**



**Fig. 4 – Typical Reverse Leakage Characteristics**



**Fig. 5 – Typical Junction Capacitance**



**Fig. 6 – Typical Transient Thermal Impedance**

